

ABSTRACT

The present disclosure relates to an epitaxial growth method and an epitaxial wafer. In an aspect, an epitaxial growth method is provided for a heavily doped substrate without a back-seal film, and the method includes: placing the heavily doped substrate on a susceptor of a reactor chamber; introducing main hydrogen gas into the reactor chamber via a first gas inlet, and introducing auxiliary hydrogen gas into a region of the reactor chamber located below the susceptor via a second gas inlet; baking the reactor chamber at a predetermined temperature; and introducing a reaction gas into the reactor chamber via the first gas inlet, to form an epitaxial layer on the heavily doped substrate by a deposition reaction, wherein at least during the baking and the deposition reaction, a flow rate of the main hydrogen gas is greater than or equal to 55 slm, or a flow rate of the auxiliary hydrogen gas is less than or equal to 18 slm.

(Figure 2)